



# STE48NM50

## N-CHANNEL 550V @ Tjmax - 0.08Ω - 48A ISOTOP MDmesh™ MOSFET

**Table 1: General Features**

TYPE	V <sub>DSS</sub> (@T <sub>jmax</sub> )	R <sub>DS(on)</sub>	I <sub>D</sub>
STE48NM50	550V	< 0.1Ω	48 A

- TYPICAL R<sub>DS(on)</sub> = 0.08Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL AND HIGH MANUFACTURING YIELDS

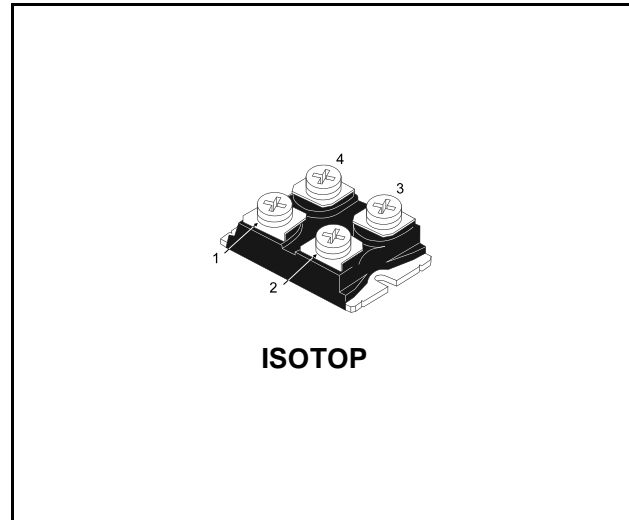
### DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

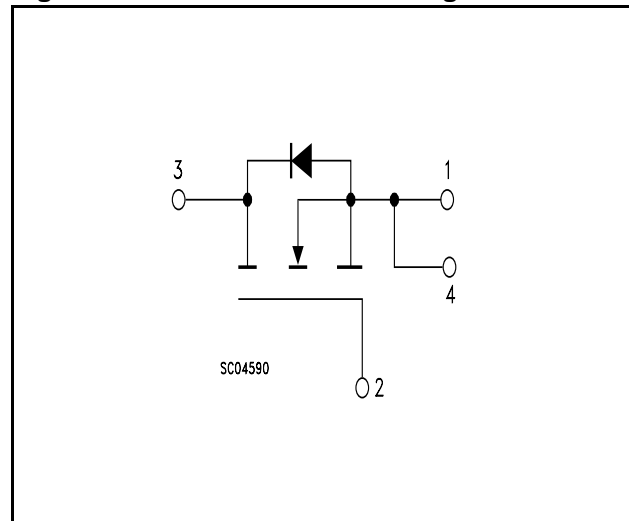
### APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.

**Figure 1: Package**



**Figure 2: Internal Schematic Diagram**



**Table 2: Order Codes**

SALES TYPE	MARKING	PACKAGE	PACKAGING
STE48NM50	E48NM50	ISOTOP	TUBE

**Table 3: Absolute Maximum ratings**

Symbol	Parameter	Value	Unit
V <sub>GS</sub>	Gate- source Voltage	±30	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	48	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	30	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	192	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	450	W
	Derating Factor	3.6	W/°C
dv/dt (*)	Peak Diode Recovery voltage slope	15	V/ns
V <sub>ISO</sub>	Insulation Withstand Voltage (AC-RMS)	2500	V
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(•)Pulse width limited by safe operating area

(\*) I<sub>SD</sub> ≤ 48A, di/dt ≤ 400 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

**Table 4: Thermal Data**

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	0.28	°C/W
R <sub>thc-sink</sub> (**)	Thermal Resistance Case-sink	Typ	0.05	°C/W

(\*\*) with conductive GREASE Applies

**Table 5: Avalanche Characteristics**

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	15	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	810	mJ

**ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> =25°C UNLESS OTHERWISE SPECIFIED)**
**Table 6: On/Off**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	500			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating			10	μA
		V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125°C			100	μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 30V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	3	4	5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 24A		0.08	0.1	Ω

## ELECTRICAL CHARACTERISTICS (CONTINUED)

Table 7: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}$ (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ , $I_D = 24A$		20		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25V$ , $f = 1$ MHz, $V_{GS} = 0$		3700 610 80		pF pF pF
$R_G$	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.7		$\Omega$
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $t_c$	Turn-on Delay Time Rise Time Turn-off Delay Time Fall Time Cross-over Time	$V_{DD} = 250V$ , $I_D = 24$ A $R_G = 4.7\Omega$ $V_{GS} = 10$ V (see Figure 14)		40 35 18 23 44		ns ns ns ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 400V$ , $I_D = 48$ A, $V_{GS} = 10V$ (see Figure 18)		87 23 42	117	nC nC nC

Table 8: Source Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				48	A
$I_{SDM}$ (2)	Source-drain Current (pulsed)				192	A
$V_{SD}$ (1)	Forward On Voltage	$I_{SD} = 48$ A, $V_{GS} = 0$			1.5	V
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 40$ A, $di/dt = 100$ A/ $\mu$ s, $V_{DD} = 100$ V, $T_j = 25^\circ C$ (see Figure 16)		520 7.8 30		ns $\mu$ C A
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 40$ A, $di/dt = 100$ A/ $\mu$ s, $V_{DD} = 100$ V, $T_j = 150^\circ C$ (see Figure 16)		680 11.2 33		ns $\mu$ C A

Note: 1. Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

Figure 3: Safe Operating Area

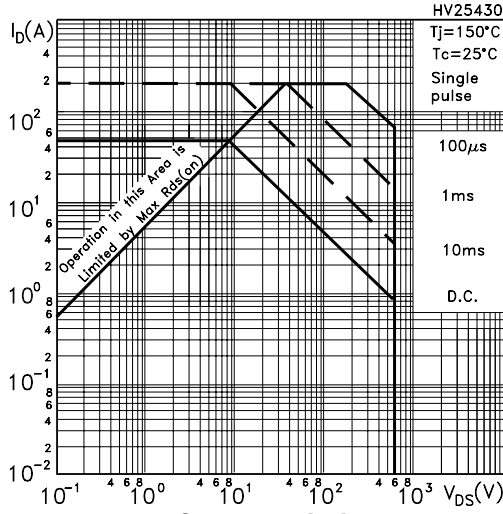


Figure 4: Output Characteristics

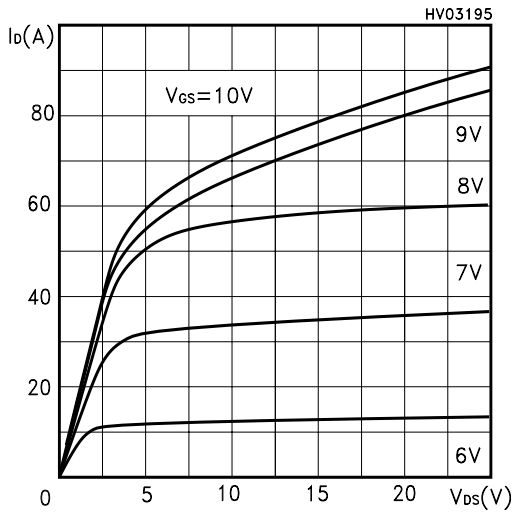


Figure 5: Transconductance

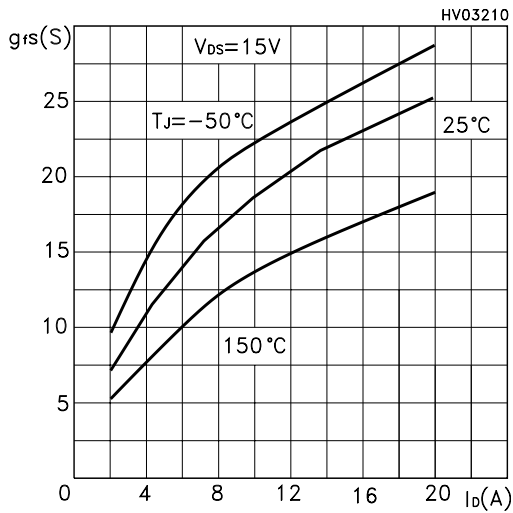


Figure 6: Thermal Impedance

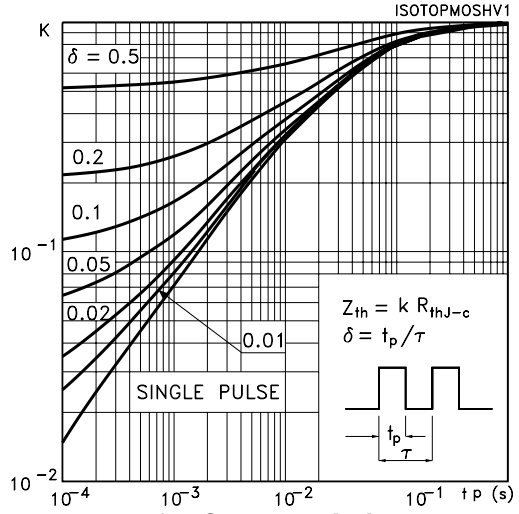


Figure 7: Transfer Characteristics

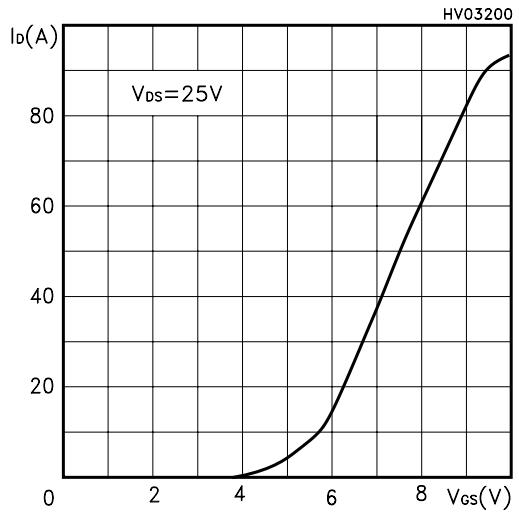


Figure 8: Static Drain-source On Resistance

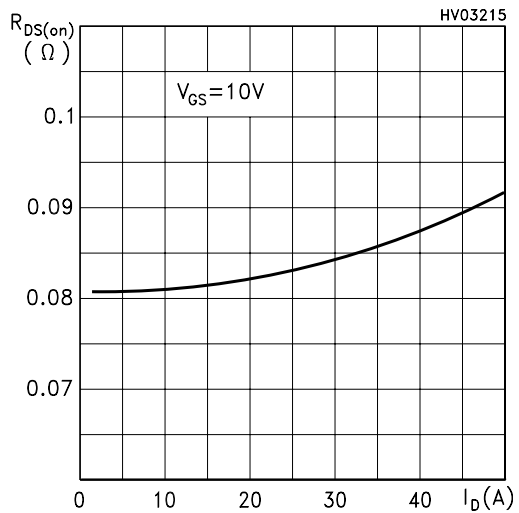


Figure 9: Gate Charge vs Gate-source Voltage

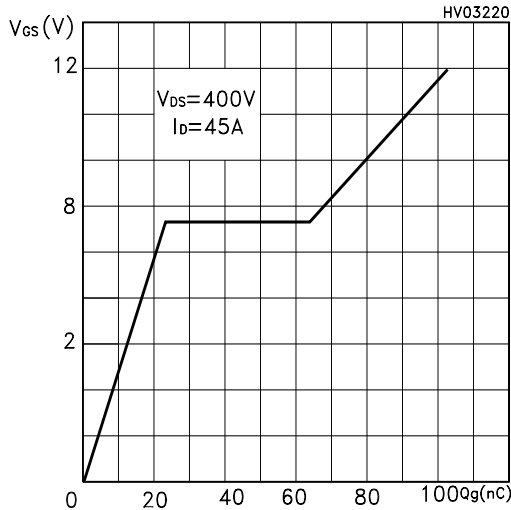


Figure 10: Normalized Gate Threshold Voltage vs Temperature

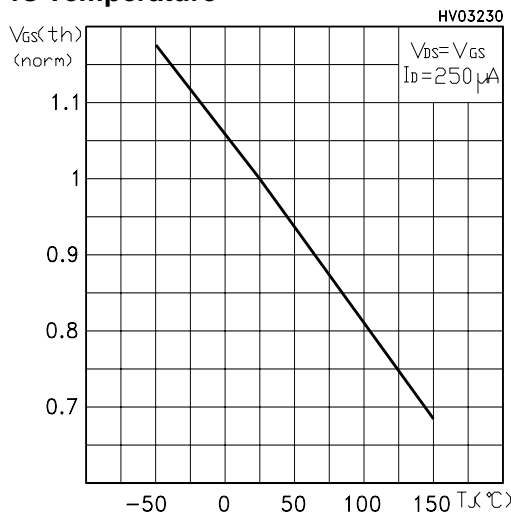


Figure 11: Source-Drain Diode Forward Characteristics

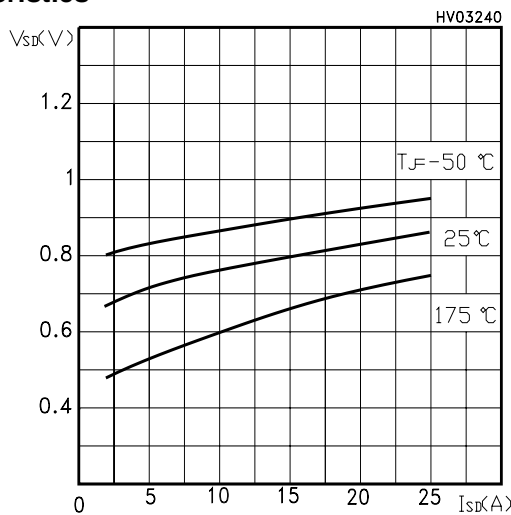


Figure 12: Capacitance Variations

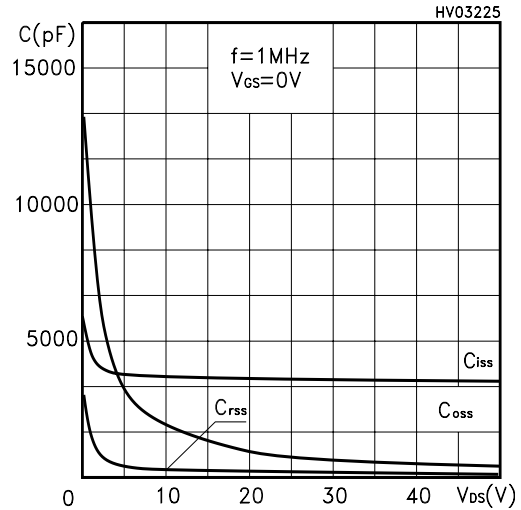


Figure 13: Normalized On Resistance vs Temperature

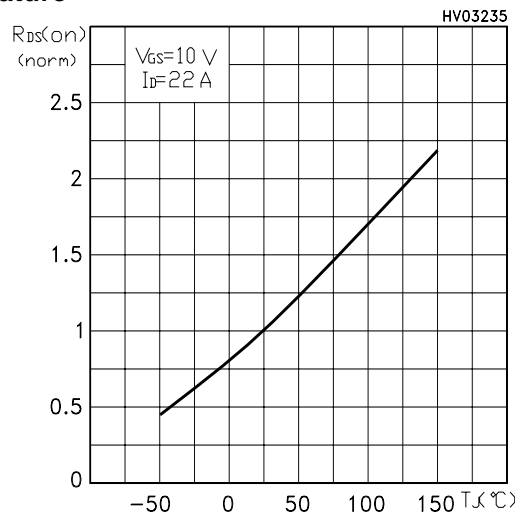


Figure 14: Unclamped Inductive Load Test Circuit

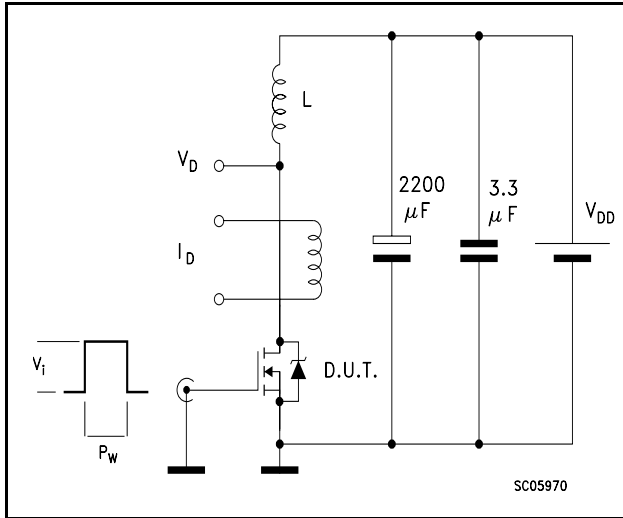


Figure 15: Switching Times Test Circuit For Resistive Load

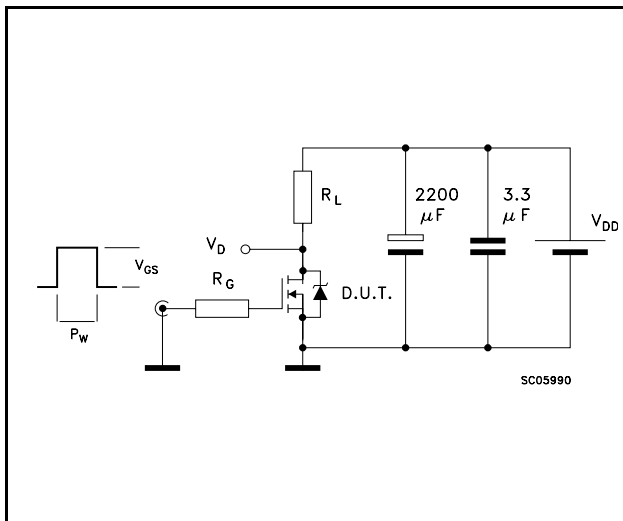


Figure 16: Test Circuit For Inductive Load Switching and Diode Recovery Times

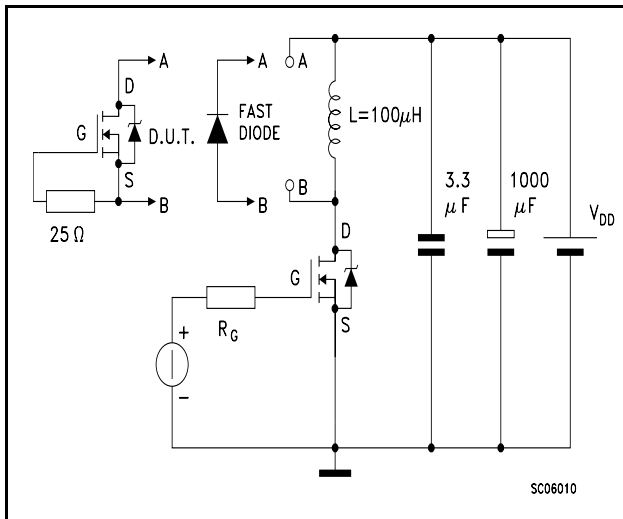


Figure 17: Unclamped Inductive Wafem

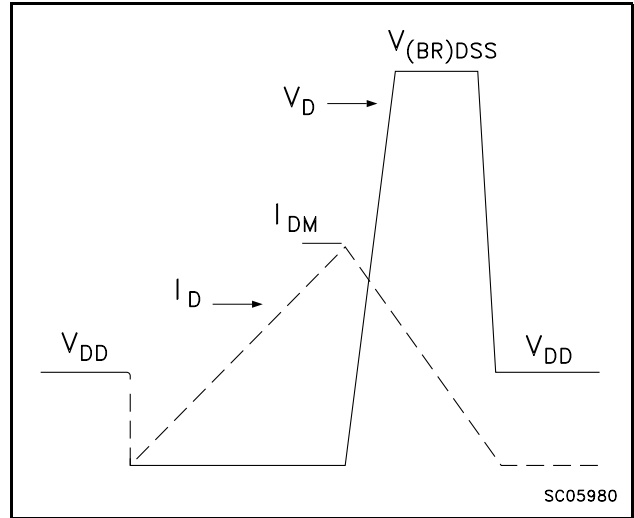
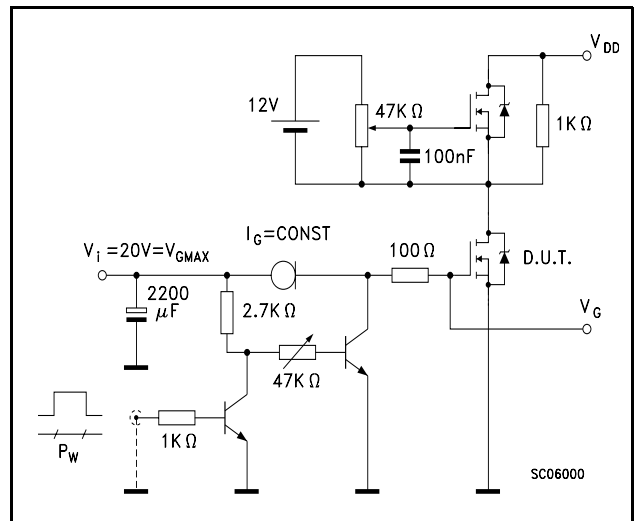
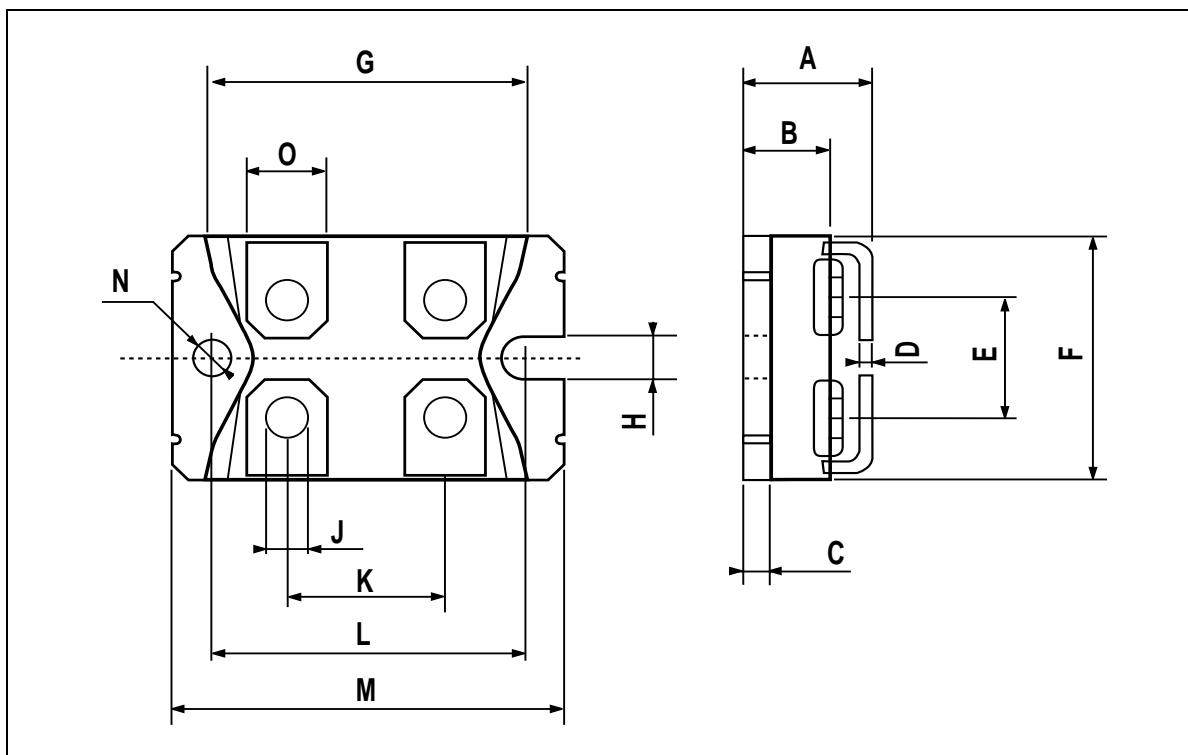


Figure 18: Gate Charge Test Circuit



## ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322



**Table 9: Revision History**

Date	Revision	Description of Changes
30/Mar/2005	2	Modified value in table 7



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